

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
60V	1.1 $\Omega$ @10V	230mA
	1.4 $\Omega$ @4.5V	

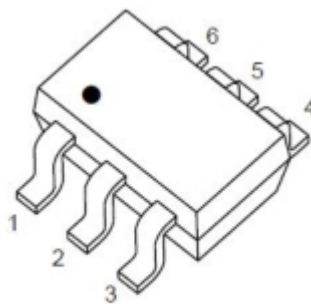
## Feature

- High density cell design for Low  $R_{DS(on)}$
- Voltage controlled small signal switch
- Rugged and reliable
- High saturation current capability

## Application

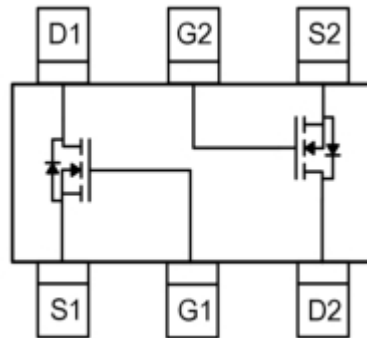
- DC/DC Converter
- Load Switch for Portable Devices

## Package

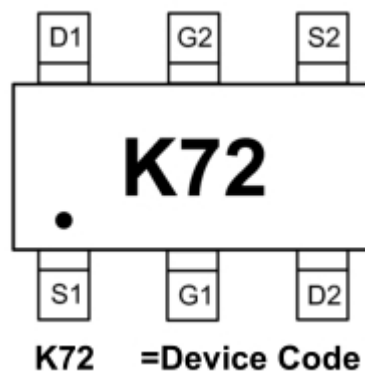


**SOT-363**

## Circuit diagram



## Marking



## Absolute maximum ratings

(T<sub>a</sub>=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	60	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Continuous Drain Current	I <sub>D</sub>	230	mA
Power Dissipation	P <sub>D</sub>	150	mW
Thermal Resistance from Junction to Ambient	R <sub>θJA</sub>	833	°C/W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55~ +150	°C

## Electrical characteristics

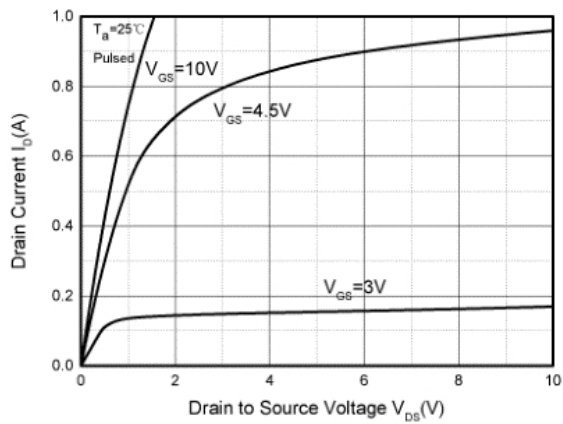
(T<sub>A</sub>=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	60			V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 48V, V_{GS} = 0V$			1	$\mu A$
Gate-body leakage current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 1$	$\mu A$
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	1.5	2.5	V
Drain-source on-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 500mA$		1.1	3	$\Omega$
		$V_{GS} = 4.5V, I_D = 200mA$		1.4	4	
Dynamic characteristics						
Input Capacitance <sup>1)</sup>	$C_{iss}$	$V_{DS} = 25V, V_{GS} = 0V, f = 1MHz$ Z			50	pF
Output Capacitance <sup>1)</sup>	$C_{oss}$				25	
Reverse Transfer Capacitance <sup>1)</sup>	$C_{rss}$				5	
Switching Characteristics						
Turn-on delay time <sup>1)</sup>	$t_{d(on)}$	$V_{DD} = 25V, R_L = 50\Omega$			20	ns
Turn-off delay time <sup>1)</sup>	$t_{d(off)}$	$I_D = 500mA, V_{GEN} = 10V,$ $R_G = 25\Omega$			40	
Source-Drain Diode Characteristics						
Diode Forward voltage	$V_{SD}$	$V_{GS} = 0V, I_S = 115mA$			1.2	V

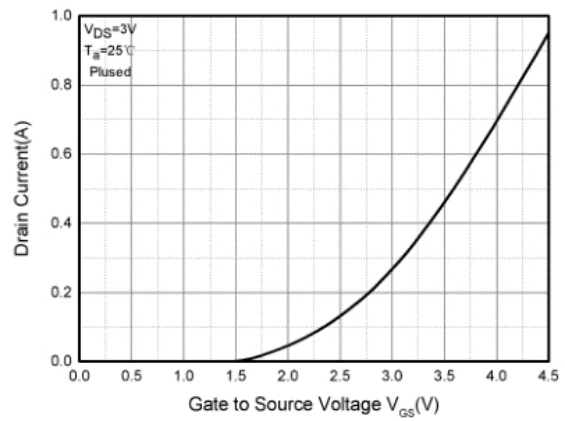
### Notes:

- These parameters have no way to verify.

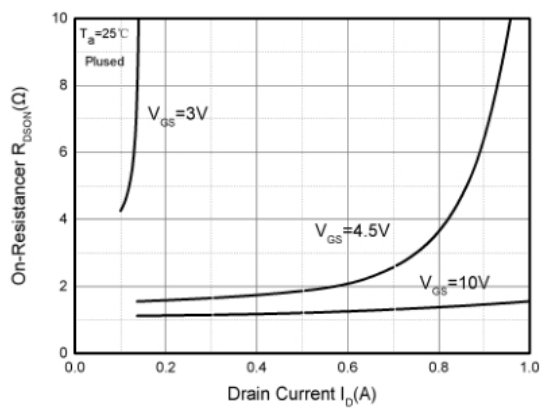
## Typical Characteristics



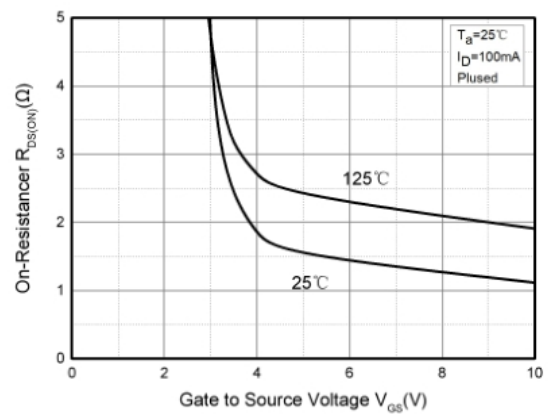
**Output Characteristics**



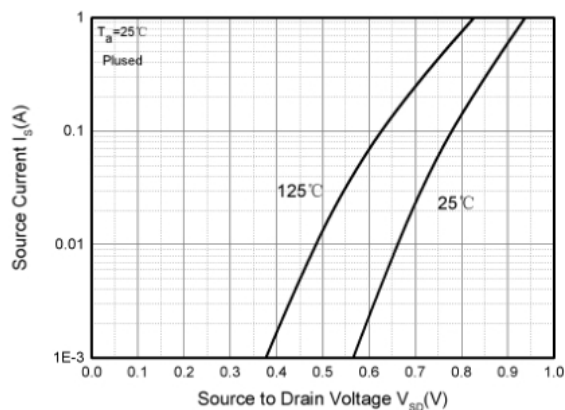
**Transfer Characteristics**



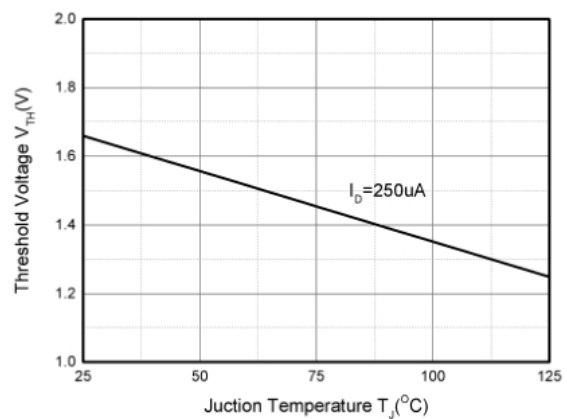
**On-Resistance vs. Drain current**



**On-Resistance vs. Gate to Source Voltage**

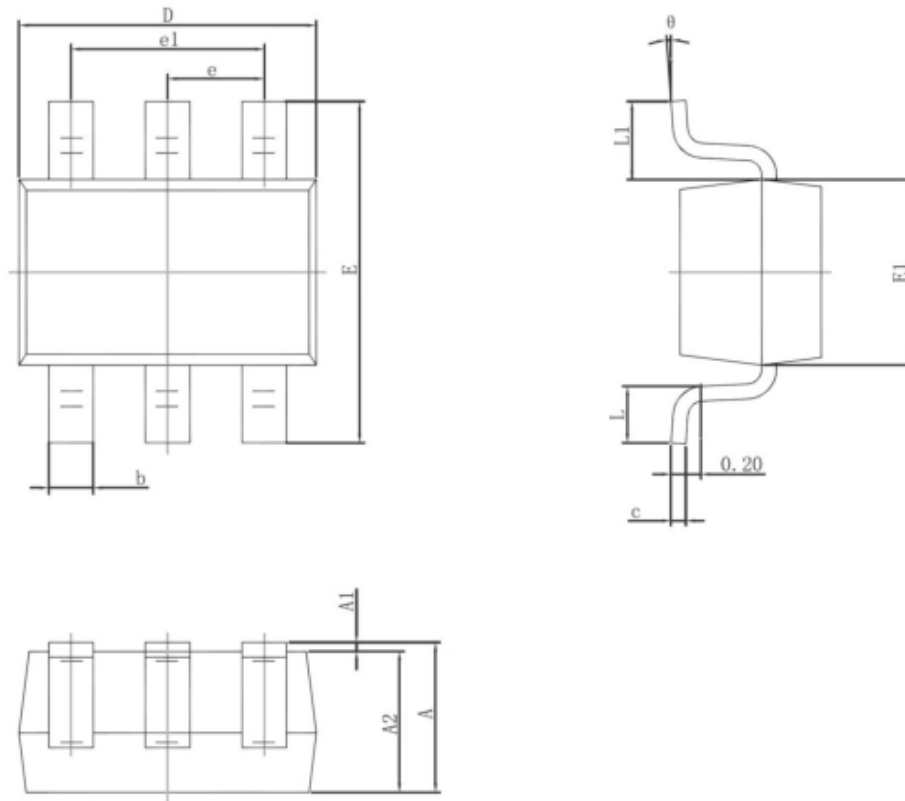


**Source Current vs. Source to Drain Voltage**



**Threshold voltage vs. Junction temperature**

## SOT-363 Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	0.90	1.10
A1	0.00	0.10
A2	0.90	1.00
b	0.15	0.35
c	0.10	0.15
D	2.00	2.20
E1	1.15	1.35
E	2.15	2.40
e	0.65 TYP.	
e1	1.20	1.40
L	0.26	0.46